

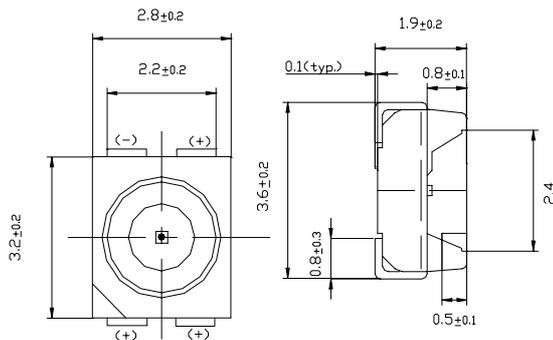
Device Selection Guide

Part Number EOS-	Luminous Intensity Iv(mcd) @ I _F = 50mA		Viewing Angle 2θ _{1/2}	Dominant Wavelength λ _D (nm) @ I _F = 50mA	Forward Voltage V _F (v) @ I _F = 50 mA		I _R (μA) @ V _R = 5V
	Min.	Typ.	Typ.	Typ.	Typ.	Max.	Max.
9ZPYCR0-KK	900	1200	120°	615	2.1	2.75	10

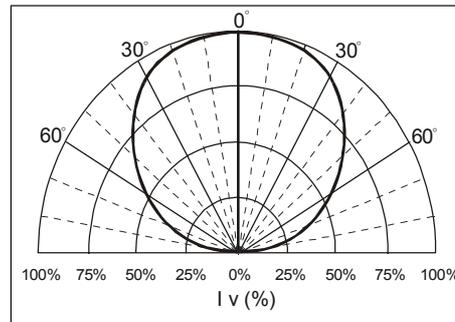
BIN #	5V	4W	5W	4X*	
Intensity (mcd) @ I _F =50mA	900-1125	1125-1400	1400-1800	1800-2240	

Note : [*] Bin with less distribution.

Package Dimensions



Beam Pattern



Note:

- All dimensions are in millimeter.
- Tolerance is ±0.20mm unless otherwise note.
- Specifications are subject to be changed without notice.

Absolute Maximum Ratings at T_A = 25°C

Parameter	Symbol	Maximum Value	USER---APPROVED
Average Forward Current	I _F	70mA	
Peak Forward Current ^[a]	I _{peak}	100mA	
Reverse Voltage	V _R	5V	
Power Dissipation	P _D	192.5mW	
Operating Temperature Range	T _{OPR}	-40°C ~ + 100°C	
Storage Temperature Range	T _{STO}	-40°C ~ + 100°C	
Lead Soldering Temperature	T _{SOL}	260°C / 5 seconds	

Notes: [a] t_p ≤ 10 μs, Duty Cycle = 0.005

Headquarters

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